

Discrete IGBTs Silicon N-Channel IGBT

# GT20N135SRA

### 1. Applications

- Dedicated to Voltage-Resonant Inverter Switching Applications
- · Dedicated to Soft Switching Applications
- · Dedicated to Induction Cooktops and Home Appliance Applications

Note: The product(s) described herein should not be used for any other application.

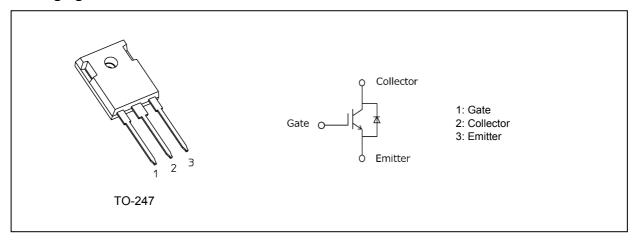
#### 2. Features

- (1) 6.5th generation
- (2) The RC-IGBT consists of a freewheeling diode (FWD) monolithically integrated in an IGBT chip.
- (3) Enhancement mode
- (4) High-speed switching:

IGBT 
$$t_f = 0.25 \mu s$$
 (typ.) ( $I_C = 40 A$ )

- (5) Low saturation voltage:  $V_{CE(sat)} = 1.60 \text{ V (typ.)}$  ( $I_C = 20 \text{ A}$ ,  $T_a = 25 ^{\circ}\text{C}$ )
- (6) High junction temperature:  $T_j = 175$  °C (max)

#### 3. Packaging and Internal Circuit



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### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C, unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Collector-emitter voltage		(Note 2)	V <sub>CES</sub>	1350	V
Gate-emitter voltage			V <sub>GES</sub>	±25	V
Collector current (DC)	(T <sub>c</sub> = 25 °C)		Ic	40	Α
Collector current (DC)	(T <sub>c</sub> = 100 °C)			20	
Collector current (1 ms)			I <sub>CP</sub>	80	Α
Non-repetitive peak collector current		(Note 1)	I <sub>CSM</sub>	220	Α
Diode forward current (DC)	(T <sub>c</sub> = 25 °C)		I <sub>F</sub>	40	Α
Diode forward current (DC)	(T <sub>c</sub> = 100 °C)			20	
Diode forward current (100 μs)			I <sub>FP</sub>	80	Α
Collector power dissipation	(T <sub>c</sub> = 25 °C)		P <sub>C</sub>	312	W
Junction temperature		(Note 2)	Tj	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	°C
Mounting torque			TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

In general, loss of IGBT increases more when it has positive temperature coefficient and gets higher temperature.

In case that the temperature rise due to loss of IGBT exceeds the heat release capacity of a device, it leads to thermorunaway and results in destruction.

Therefore, please design heat release of a device with due consideration to the temperature rise of IGBT.

- Note 1: The maximum value of the capacitor charging current limited on  $T_i$  < 175 °C and t < 3  $\mu$ s
- Note 2: To perform derating ensures the device reliability.

In operation, the collector emitter voltage(V<sub>CES</sub>) should be below 1150 V, as well as junction temperature(T<sub>i</sub>) should be below 140 °C.

#### 5. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Jur	Junction-to-case thermal resistance		0.48	°C/W



### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C, unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GES</sub>	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0 \text{ V}$	_	_	±100	nA
Collector cut-off current	I <sub>CES</sub>	V <sub>CE</sub> = 1350 V, V <sub>GE</sub> = 0 V	_	_	100	μΑ
Collector-emitter breakdown voltage	V <sub>(BR)CES</sub>	$I_C = 0.5 \text{ mA}, V_{GE} = 0 \text{ V}$	1350	_		V
Gate-emitter cut-off voltage	V <sub>GE(OFF)</sub>	I <sub>C</sub> = 40 mA, V <sub>CE</sub> = 5 V	5.3	_	7.3	V
Collector-emitter saturation voltage	V <sub>CE(sat)(1)</sub>	I <sub>C</sub> = 20 A, V <sub>GE</sub> = 15 V (pulse test)		1.60	1.80	٧
	V <sub>CE(sat)(2)</sub>	$I_C$ = 20 A, $V_{GE}$ = 15 V, $T_c$ = 125 °C (pulse test)		1.83		
	V <sub>CE(sat)(3)</sub>	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V (pulse test)	_	2.00	2.40	
	V <sub>CE(sat)(4)</sub>	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V, T <sub>c</sub> = 125 °C (pulse test)	_	2.40		
Diode forward voltage	V <sub>F(1)</sub>	$I_F = 20 \text{ A}, V_{GE} = 0 \text{ V}$ (pulse test)	_	1.75	2.50	V
	V <sub>F(2)</sub>	$I_F = 20 \text{ A}, V_{GE} = 0 \text{ V},$ $T_c = 125 ^{\circ}\text{C} \text{ (pulse test)}$	_	1.80	_	



### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C, unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V,	_	2700	_	pF
Reverse transfer capacitance	C <sub>res</sub>	f = 100 kHz	_	35	_	
Output capacitance	C <sub>oes</sub>		_	42	_	
Total gate charge	Qg	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	_	185	_	nC
Switching time (rise time)	t <sub>r</sub>	Resistive load	_	0.09	_	μS
Switching time (turn-on time)	t <sub>on</sub>	$V_{CE}$ = 600 V, $I_{C}$ = 40 A, $V_{GE}$ = +15 V, $R_{G}$ = 10 $\Omega$ See Fig. 6.2.1, 6.2.2	_	0.14	_	
Switching time (fall time)	t <sub>f</sub>		_	0.25	0.40	
Switching time (turn-off time)	t <sub>off</sub>		_	0.46	_	
Switching loss (turn-off switching loss)	E <sub>off(1)</sub>	Inductive load $V_{CE} = 300 \text{ V, } I_{C} = 40 \text{ A,} \\ V_{GE} = +15 \text{ V, } R_{G} = 39 \Omega \\ L = 30 \ \mu\text{H, } C = 0.33 \ \mu\text{F} \\ \text{See Fig. 6.2.3, 6.2.4}$	_	0.28	_	mJ
	E <sub>off(2)</sub>	Inductive load $V_{CE} = 300 \text{ V}, I_{C} = 40 \text{ A}, \\ V_{GE} = +15 \text{ V}, R_{G} = 39 \Omega, \\ L = 30 \ \mu\text{H}, C = 0.33 \ \mu\text{F} \\ T_{c} = 125 \ ^{\circ}\text{C} \\ \text{See Fig. 6.2.3, 6.2.4}$	_	0.70	_	

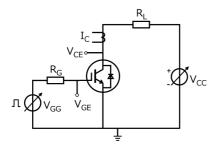


Fig. 6.2.1 Test Circuit of Switching Time

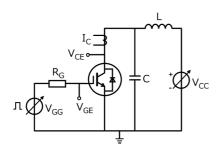


Fig. 6.2.3 Test Circuit of Switching Loss

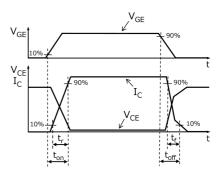


Fig. 6.2.2 Timing Chart of Switching Time

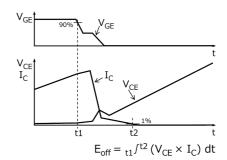


Fig. 6.2.4 Timing Chart of Switching Loss



### 7. Marking (Note)

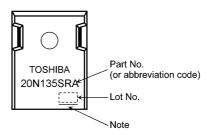


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



### 8. Characteristics Curves (Note)

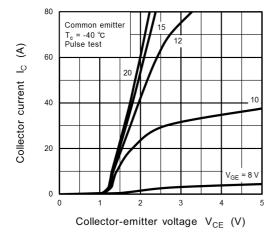


Fig. 8.1 Ic - VCE

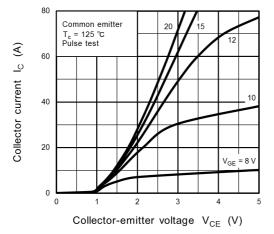


Fig. 8.3 I<sub>C</sub> - V<sub>CE</sub>

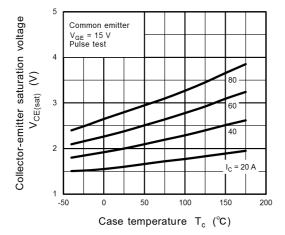


Fig. 8.5 V<sub>CE(sat)</sub> - T<sub>c</sub>

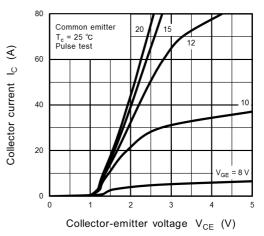


Fig. 8.2 I<sub>C</sub> - V<sub>CE</sub>

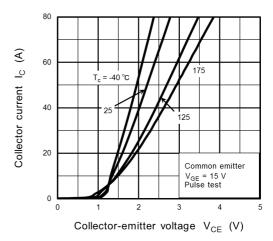


Fig. 8.4 I<sub>C</sub> - V<sub>CE</sub>

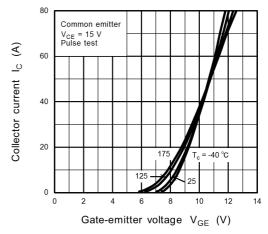


Fig. 8.6 I<sub>C</sub> - V<sub>GE</sub>



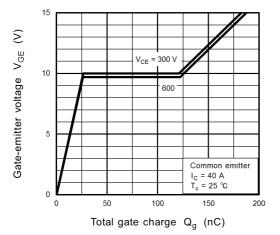


Fig. 8.7  $V_{GE}$  -  $Q_g$ 

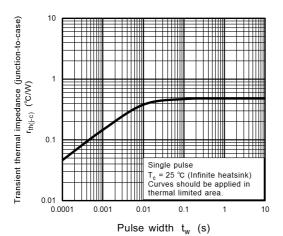


Fig. 8.9  $r_{th(j-c)}$  -  $t_w$  (Guaranteed Maximum)

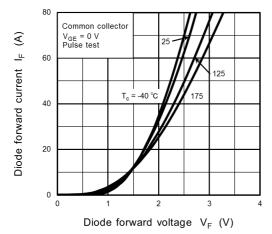


Fig. 8.11 I<sub>F</sub> - V<sub>F</sub>

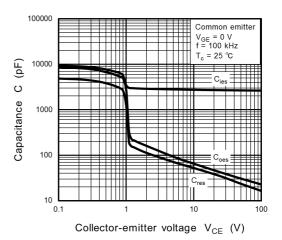


Fig. 8.8 C-V<sub>CE</sub>

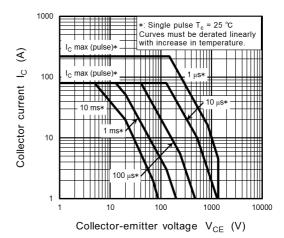


Fig. 8.10 Safe Operating Area (Guaranteed Maximum)

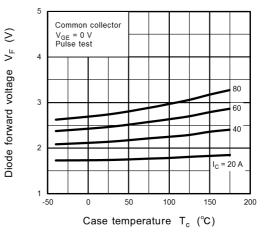


Fig. 8.12 V<sub>F</sub> - T<sub>C</sub>



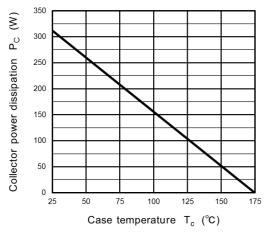
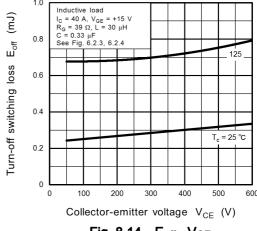


Fig. 8.13 Pc - Tc



1.0

Fig. 8.14 Eoff - VCE

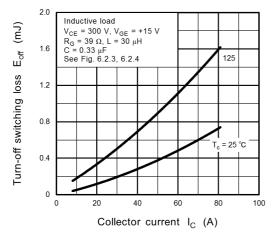
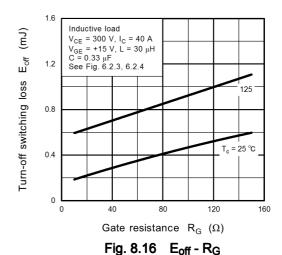


Fig. 8.15 E<sub>off</sub> - I<sub>C</sub>



1.6 Inductive load (m) Middetive load  $V_{CE} = 300 \text{ V}, I_{C} = 40 \text{ A}$   $V_{GE} = +15 \text{ V}, R_{G} = 39 \Omega$  L = 30  $\mu$ H, C = 0.33  $\mu$ F See Fig. 6.2.3, 6.2.4 ⊎ E 1.2 Turn-off switching loss 0.8 0.4 0 0 Case temperature T<sub>c</sub> (°C)

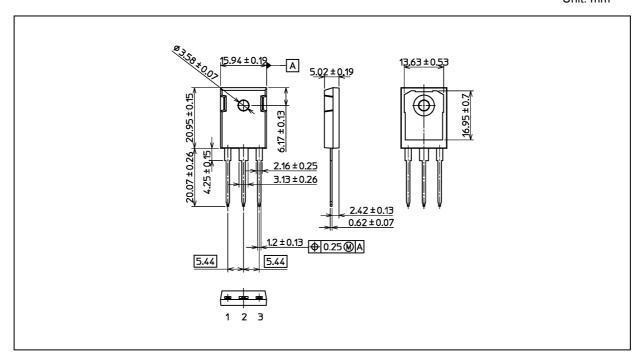
Fig. 8.17 E<sub>off</sub> - T<sub>c</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 6.15 g (typ.)

	Package Name(s)
TOSHIBA: 2-16L1A	
Nickname: TO-247	

Rev.2.0



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